

**SuperMOS – TO-252 -30V  $BV_{DSS}$ ,  $8m\Omega$   $R_{DS(ON)}$ , -62A  $I_D$  P-channel MOSFET**

**1. Description**

The AOD403 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AOD403 is Pb-free.

**2. Features**

- -30V,  $R_{DS(ON)}=8m\Omega$ ,  $V_{GS}=-10V$
- $R_{DS(ON)}=11.5m\Omega$ ,  $V_{GS}=-4.5V$
- Fast Switching
- High density cell design for low  $R_{DS(on)}$
- Material : Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

**3. Applications**

- PWM applications **100% UIS TESTED!**
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**4. Ordering Information**

Part Number	Package	Marking	Material	Quantity per reel	Flammability Rating
AOD403	TO-252	ESD403/lot	Halogen free	2,500 PCS	UL 94V-0

Table-1 Ordering information

**5. Pin Configuration and Functions**

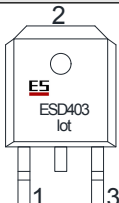
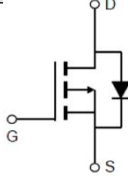
Pin	Function	Outline	Circuit Diagram
1	Gate		
3	Source		
2	Drain		

Table-2 Pin configuration

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$BV_{DSS}$	-30	V	
Gate-Source Voltage	$V_{GS}$	±25	V	
Continuous Drain Current <sup>a</sup>	$I_D$	$T_C=25^{\circ}C$	-62	A
		$T_C=75^{\circ}C$	-48	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_C=25^{\circ}C$	79	W
		$T_C=75^{\circ}C$	47	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	-200	A	
Avalanche Current, Single Pulsed <sup>c</sup>	$I_{AS}$	24	A	
Avalanche Energy, Single Pulsed <sup>c</sup>	$E_{AS}$	86.4	mJ	
Operating Junction Temperature	$T_J$	150	°C	
Storage Temperature Range	$T_{stg}$	-55 to +150	°C	

#### Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance <sup>a</sup>	$t \leq 10$ s	$R_{\theta JA}$	16	20	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	0.9	1.6	

#### Note:

a: Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b: Repetitive rating, pulse width limited by junction temperature,  $t_p=10\mu s$ , Duty Cycle=1%

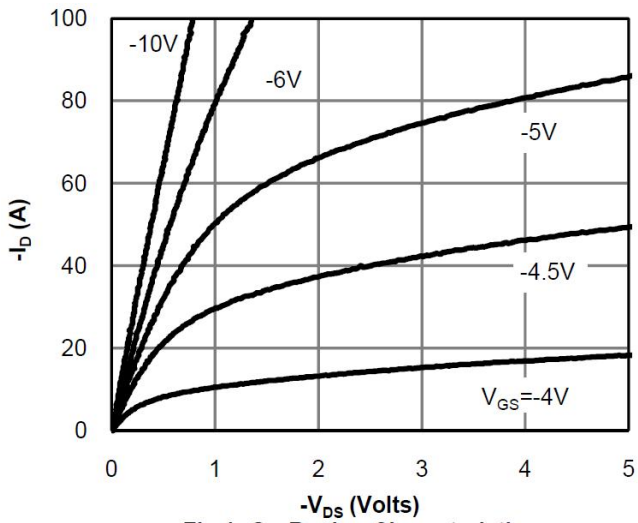
c: EAS condition:  $T_J=25^{\circ}C$ ,  $V_{DD}=-30V$ ,  $V_G=-10V$ ,  $L=0.3mH$ ,  $R_g=25\Omega$

## Electrical Characteristics

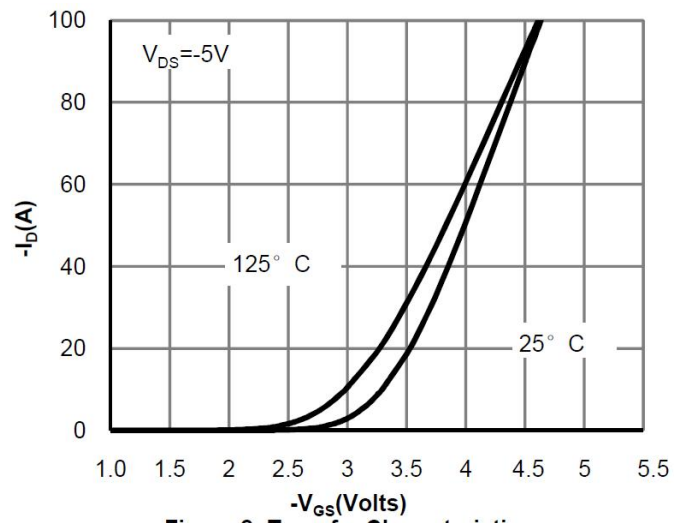
At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 25V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1	-1.5	-2	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$		8	12	m $\Omega$
		$V_{GS}=-4.5V, I_D=-20A$		11.5	18	
Forward Trans conductance	$g_{FS}$	$V_{DS}=-5.0V, I_D=-20A$			80	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, f=1MHz,$ $V_{DS}=15V$		2890	3500	pF
Output Capacitance	$C_{OSS}$			585	760	
Reverse Transfer Capacitance	$C_{RSS}$			470	660	
Gate Resistance	$R_g$	$f=1MHz$		3.8	5.7	$\Omega$
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-20A$		51	61	nC
Gate-to-Source Charge	$Q_{GS}$			12	14	
Gate-to-Drain Charge	$Q_{GD}$			16	22	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $R_L=1\Omega, R_G=3\Omega$		16		ns
Rise Time	$t_r$			12		
Turn-Off Delay Time	$t_{d(OFF)}$			45		
Fall Time	$t_f$			22		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1.0A$		-0.7	-1	V

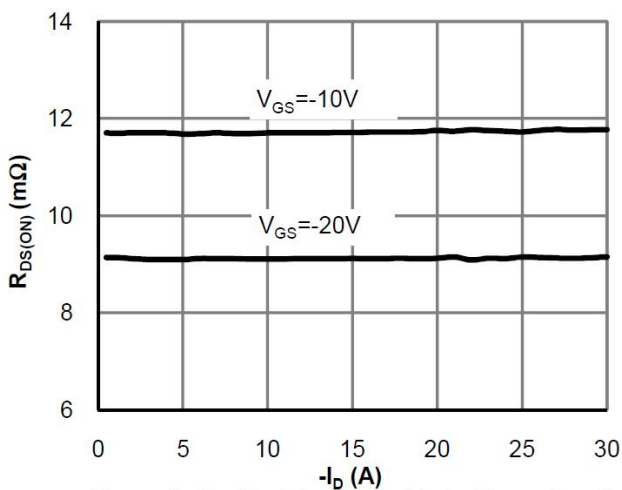
**7. Typical Characteristic**



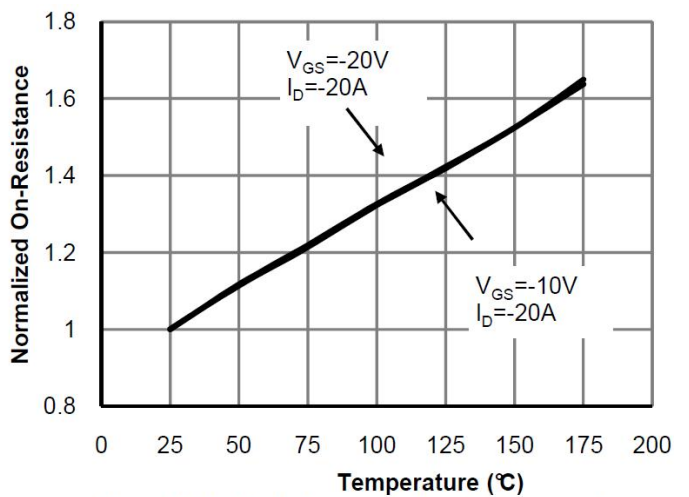
**Fig 1: On-Region Characteristics**



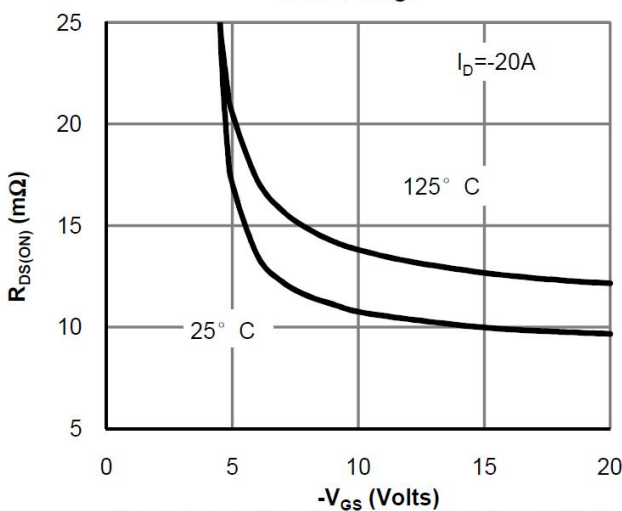
**Figure 2: Transfer Characteristics**



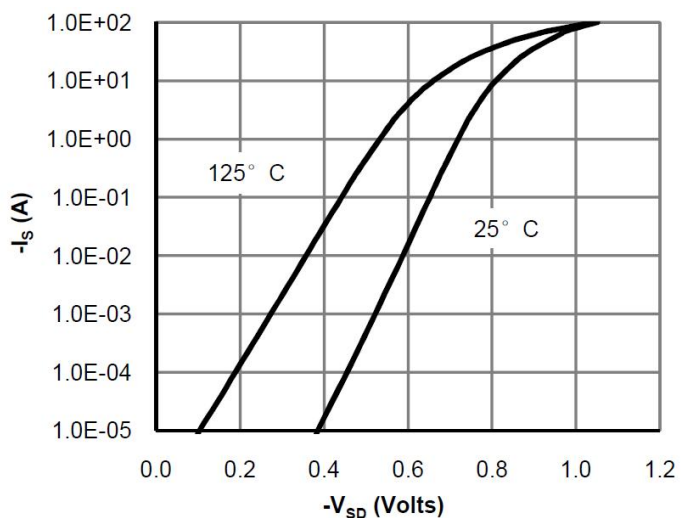
**Figure 3: On-Resistance vs. Drain Current and Gate voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5: On-Resistance vs. Gate-Source Voltage**



**Figure 6: Body-Diode Characteristics**

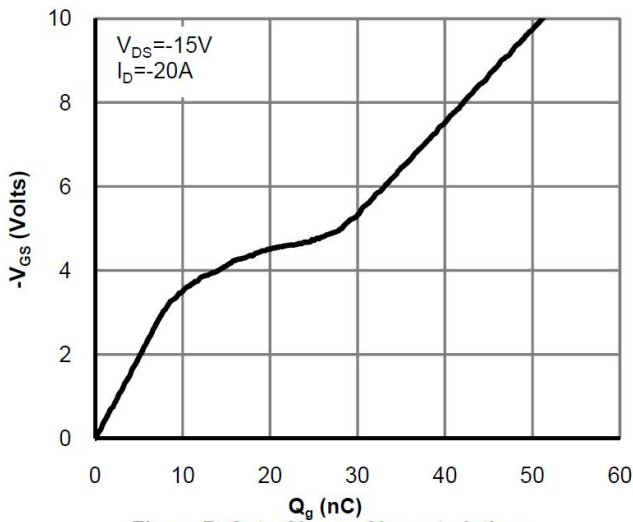


Figure 7: Gate-Charge Characteristics

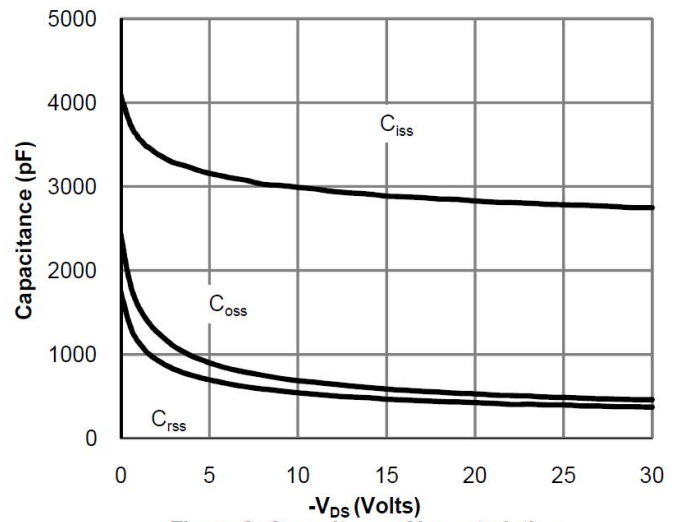


Figure 8: Capacitance Characteristics

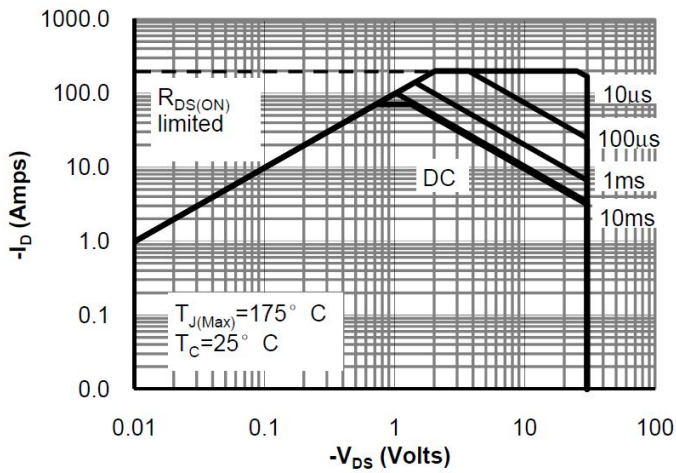


Figure 9: Maximum Forward Biased Safe Operating Area

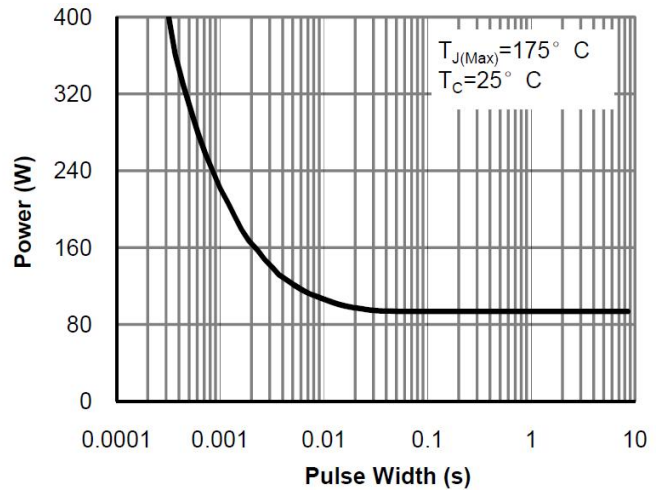


Figure 10: Single Pulse Power Rating Junction-to-Case

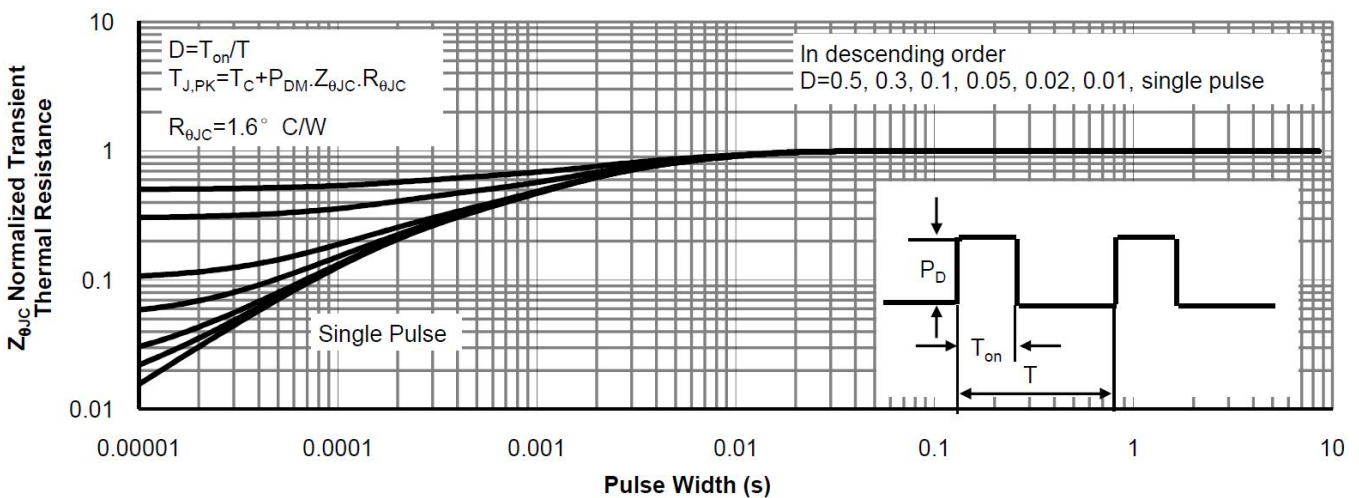
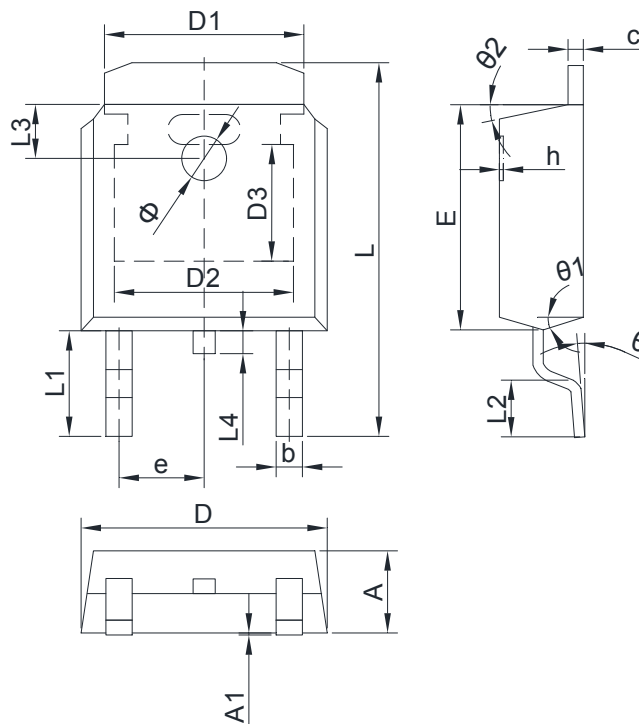


Figure 11: Normalized Maximum Transient Thermal Impedance

**8. Dimension and Patterns (TO-252)**



SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	Typ.	MAX		MIN	Typ.	MAX
A	2.200	2.300	2.400	h	0.000	0.100	0.200
A1	0.000		0.127	L	9.900	10.100	10.300
b	0.640	0.690	0.740	L1	2.888 REF		
C(电镀后)	0.460	0.520	0.580	L2	1.400	1.550	1.700
D	6.500	6.600	6.700	L3	1.600 REF		
D1	5.334 REF			L4	0.600	0.800	1.000
D2	4.826 REF			Φ	1.100	1.200	1.300
D3	3.166 REF			θ	0°		8°
E	6.000	6.100	6.200	θ1	9° TYP		
e	2.286 TYP			θ2	9° TYP		

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